MOS FET

FC4B21320L1

Panasonic

FC4B21320L1

Gate resistor installed Dual N-channel MOS FET

For lithium-ion secondary battery protection circuits

■ Features

- Source-source ON resistance:Rss(on) typ. = 39 mΩ(VGS = 3.8 V)
- CSP(Chip Size Package)
- RoHS compliant (EU RoHS / MSL:Level 1 compliant)

■ Marking Symbol: 2D

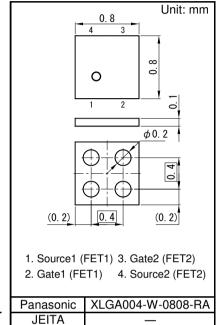
■ Packaging

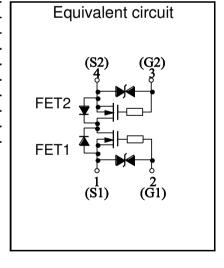
Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Source-source Voltage	VSS	12	V
Gate-source Voltage	VGS	±8	V
Source Current (DC)	IS *1	2.5	Α
	IS *2	4	Α
Source Current (Pulsed)	ISp *3	25	Α
Total Power Dissipation	PD *1	0.34	W
	PD *2	0.9	W
Channel Temperature	Tch	150	°C
Storage Temperature Range	Tstg	-55 to +150	°C
Thermal Resistance (ch-a)	Rth *1	368	°C/W
	Rth *2	139	°C/W

- Note *1 Mounted on FR4 board ($25.4~\text{mm} \times 25.4~\text{mm} \times t1.0~\text{mm}$) using the minimum recommended pad size ($36\mu\text{m}$ Copper).
 - *2 Mounted on Ceramic substrate (70 mm \times 70 mm \times t1.0 mm).
 - *3 $t = 10 \mu s$, Duty Cycle $\leq 1 \%$





Code

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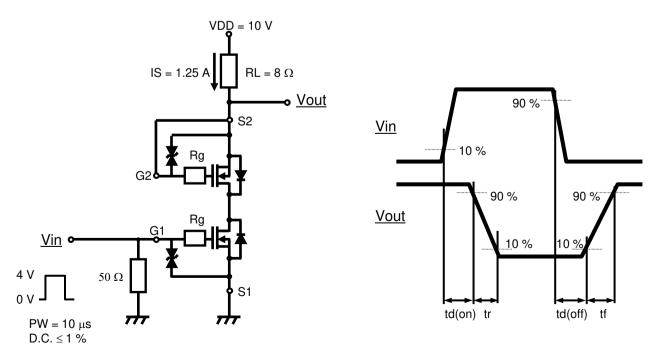
■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Source-source Breakdown Voltage	VSSS	IS = 1 mA, VGS = 0 V	12			V
Zero Gate Voltage Source Current	ISSS	VSS = 12 V, VGS = 0 V			1.0	μΑ
Gate-source Leakage Current	IGSS	VGS = ±8 V, VSS = 0 V			±10	μА
		$VGS = \pm 5 V$, $VSS = 0 V$			±1.0	
Gate-source Threshold Voltage	Vth	IS = 0.07 mA, VSS = 10 V	0.35	0.9	1.4	V
Source-source On-state Resistance	RSS(on)1	IS = 1.25 A, VGS = 4.5 V	27	36	48	mΩ
	RSS(on)2	IS = 1.25 A, VGS = 3.8 V	29	39	53	
	RSS(on)3	IS = 1.25 A, VGS = 3.1 V	32	45	75	
	RSS(on)4	IS = 1.25 A, VGS = 2.5 V	35	58	115	
Body Diode Forward Voltage	VF(s-s)	IF = 1.25 A, VGS = 0 V		0.6	1.2	V
Input Capacitance *1	Ciss			205		
Output Capacitance *1	Coss	VSS = 10 V, VGS = 0 V, f = 1 MHz		50		pF
Reverse Transfer Capacitance *1	Crss			40		
Turn-on delay Time *1,*2	td(on)	VDD = 10 V, VGS = 0 to 4.0 V		0.10		
Rise Time *1,*2	tr	IS = 1.25 A		0.15		μS
Turn-off delay Time *1,*2	td(off)	VDD = 10 V, VGS = 4.0 to 0 V		0.50		
Fall Time *1,*2	tf	IS = 1.25 A		0.30		μS
Total Gate Charge *1	Qg	VDD = 10 V		3.5		
Gate-source Charge *1	Qgs	VGS = 0 to 4.0 V,		0.8		nC
Gate-drain Charge *1	Qgd	IS = 1.25 A		1.0		

Note Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

- *1 Guaranteed by design, not subject to production testing
- *2 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

Note2: Measurement circuit



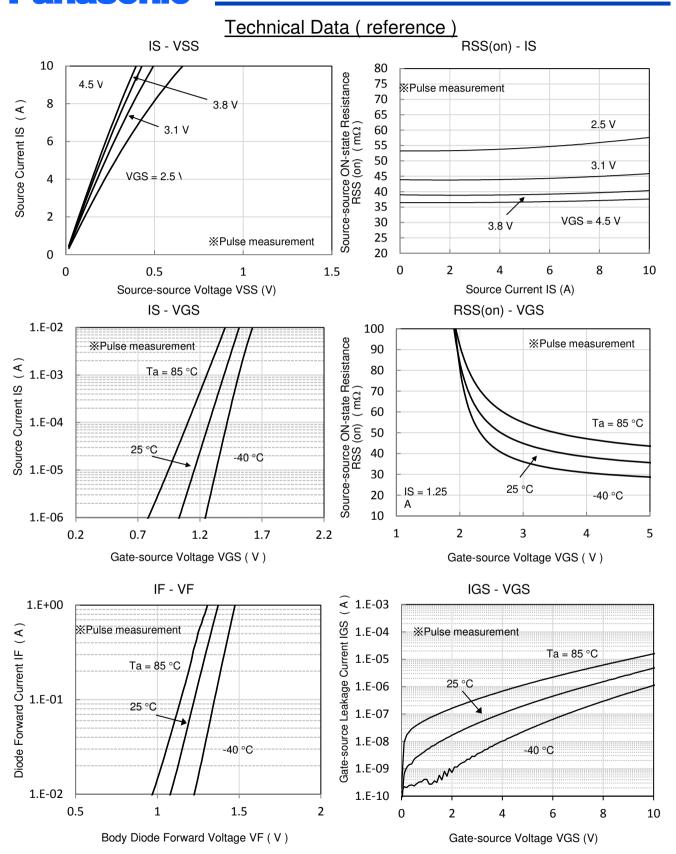
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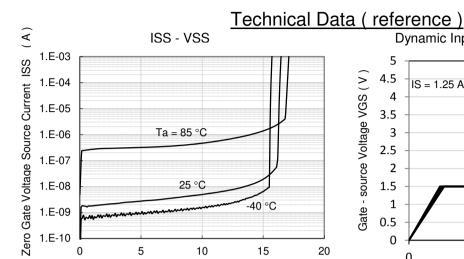


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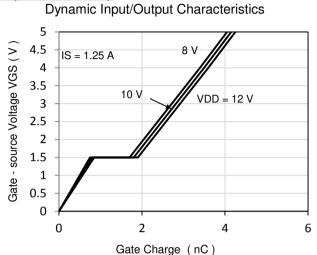
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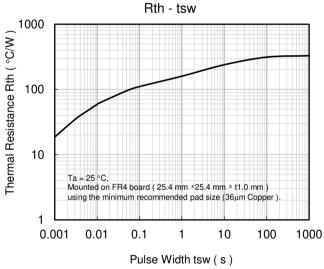
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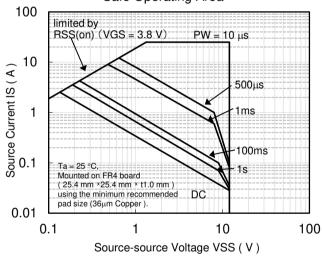


Source-source Voltage VSS (V)



Safe Operating Area





Normalized Effective Transient Thermal Impedance Thermal Response 10 1 Duty Cycle = 0.5 0.2 0.1 Single Pulse 0.01 Ta = 25 °C Mounted on FR4 board (25.4 mm ×25.4 mm × t1.0 mm) using the minimum recommended pad size (36µm Copper) 0.0001 0.001 0.01 100

Square Wave Pulse Duration (s)

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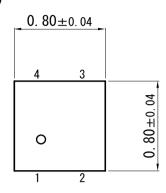
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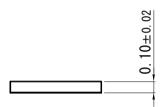
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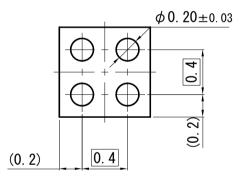
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■ Outline (XLGA004-W-0808-RA)

Unit: mm

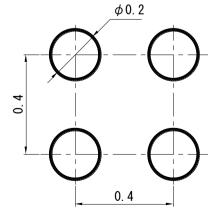






■ Land Pattern (Reference)

Unit: mm



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